

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Canceled)

Claim 2 (Currently Amended): A method of manufacturing a semiconductor device, comprising:

forming a gate electrode on a silicon substrate;

forming a first spacers on respective side surfaces of the gate electrode;

chipping off a surface of the silicon substrate using the gate electrode and the first spacers as masks, to thereby form steplike portions at positions adjacent to base portions of the first spacers;

forming second spacers respectively at the steplike portions; and

forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 1,~~

wherein the steplike portions are respectively formed so as to have upward slanting surfaces.

Claim 3 (Canceled)

Claim 4 (Currently Amended): A method of manufacturing a semiconductor device,
comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the
first spacers as masks, to thereby form steplike portions at positions adjacent to base
portions of the first spacers;
forming second spacers respectively at the steplike portions; and
forming silicides on the silicon substrate using the first spacers and the second
spacers as masks ~~The method according to claim 1,~~

wherein the steplike portions are respectively formed so as to have curved
surfaces convex to the gate electrode.

Claim 5 (Currently Amended): A method of manufacturing a semiconductor device,
comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the
first spacers as masks, to thereby form steplike portions at positions adjacent to base
portions of the first spacers;
forming second spacers respectively at the steplike portions; and

forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 1,~~
wherein the steplike portions are respectively formed so as to have downward slanting surfaces.

Claims 6-10 (Canceled)

Claim 11 (Currently Amended): A method of manufacturing a semiconductor device,
comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the first spacers as masks, to thereby form steplike portions at positions adjacent to base portions of the first spacers;

forming second spacers respectively at the steplike portions; and
forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 10,~~

wherein ~~said forming the formation of the second spacers is done by~~ comprises

forming an oxide film for covering the surface of that covers the silicon substrate, the gate electrode, and the first spacers, thereafter

covering portions other than a device region[[,]] of the silicon substrate

surface with a resist pattern and

anisotropically etching the oxide film ~~in this condition~~ using the resist.